

2SC5346

Silicon NPN epitaxial planer type

For low-frequency high breakdown voltage amplification

Complementary to 2SA1982

Features

- Satisfactory linearity of forward current transfer ratio h_{FE} .
- High collector to emitter voltage V_{CEO} .
- Small collector output capacitance C_{ob} .

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	150	V
Collector to emitter voltage	V_{CEO}	150	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	100	mA
Collector current	I_C	50	mA
Collector power dissipation	P_C^{*1}	1.0	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C

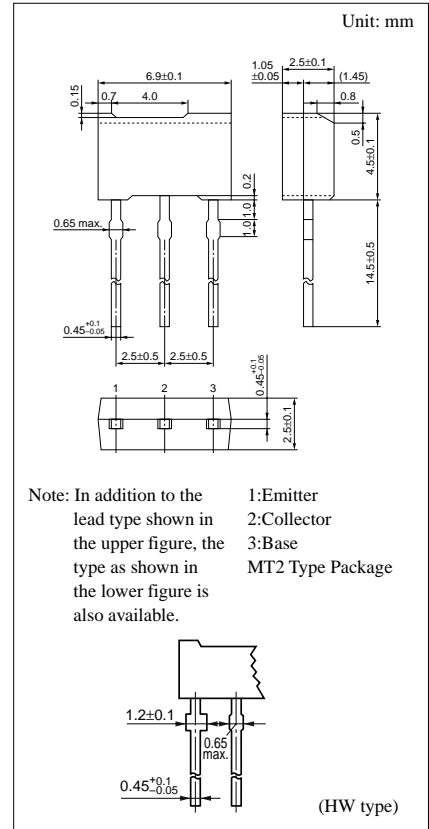
*1 Printed circuit board: Copper foil area of 1cm² or more, and the board thickness of 1.7mm for the collector portion

Electrical Characteristics (Ta=25°C)

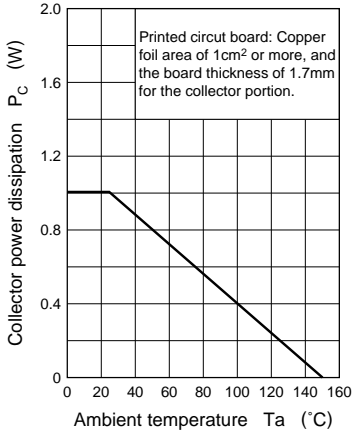
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 100V, I_E = 0$			1	μA
Collector to emitter voltage	V_{CEO}	$I_C = 0.1mA, I_B = 0$	150			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	h_{FE}^{*1}	$V_{CE} = 5V, I_C = 10mA$	130		330	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 30mA, I_B = 3mA$			1	V
Noise voltage	NV	$V_{CE} = 10V, I_C = 1mA, G_V = 80dB$ $R_g = 100k\Omega, \text{Function} = \text{FLAT}$		150	300	mV
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$		160		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$			5	pF

*1 h_{FE} Rank classification

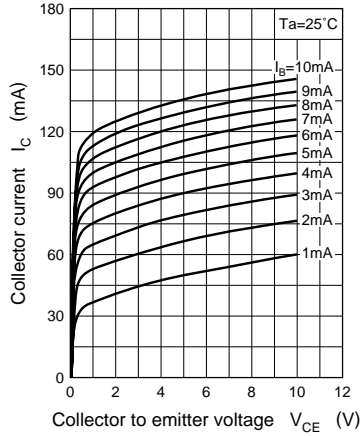
Rank	R	S
h_{FE}	130 ~ 220	185 ~ 330



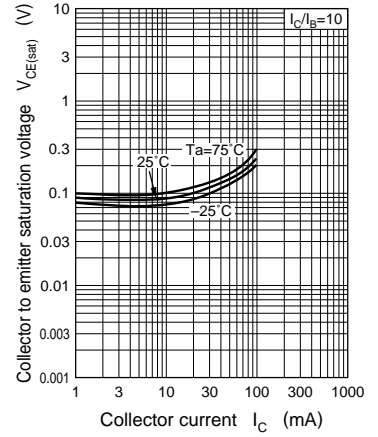
$P_C - T_a$



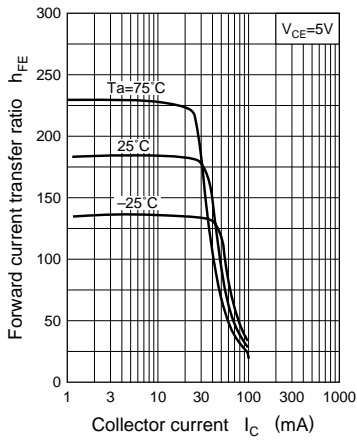
$I_C - V_{CE}$



$V_{CE(sat)} - I_C$



$h_{FE} - I_C$



$C_{ob} - V_{CB}$

